

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Please replace the paragraphs that begin on line 21 of page 2 and end on line 25 of page 4 with the following paragraph:

2  
A

A pattern correcting method of a mask for manufacturing a semiconductor device according to an aspect of the present invention comprises extracting a correction portion to be corrected from a mask pattern on the mask, obtaining a surrounding environment of the correction portion, and giving a variable correction amount to the correction portion in accordance with the surrounding environment.

**IN THE ABSTRACT:**

Please delete the Abstract in its entirety and replace it with the Abstract shown on the page attached to this Amendment.

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com